

# SONY CXK5814P

## 2048-word × 8 bit High Speed CMOS Static RAM

### Description

The CXK5814P is a 16,384 bits high speed CMOS static RAM organized as 2,048 words × 8 bits and operates from a single 5V supply.

The CXK5814P is suitable for use in high speed and low power applications in which battery back up for nonvolatility is required.

### Features

- Fast access time: 35 ns/45 ns/55 ns (Max.)
- Low power standby: 5  $\mu$ W (Typ.)—L-version  
100  $\mu$ W (Typ.)—Standard version
- Low power operation: 300 mW (Typ.)
- Single +5V supply
- Fully static memory . . . . No clock or timing strobe required
- Equal access and cycle time
- Common data input and output: three-state output
- Directly TTL compatible: All inputs and outputs
- Low voltage data retention: 2.0V (Min.)
- High density: 300 mil 24 pin plastic package

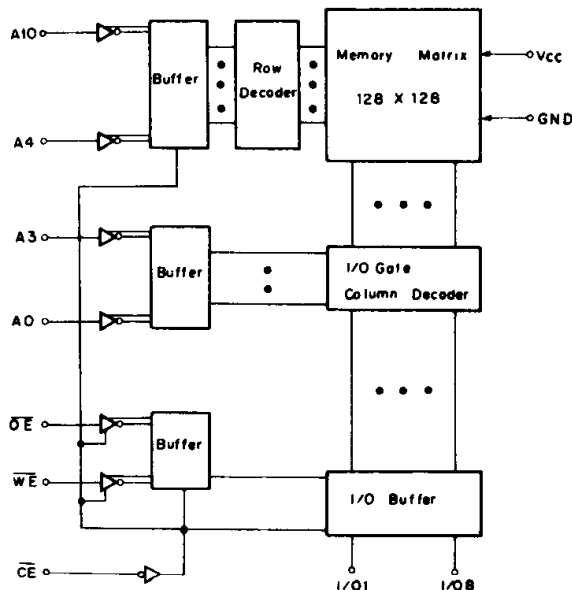
### Function

2048-word × 8 bit static RAM

### Structure

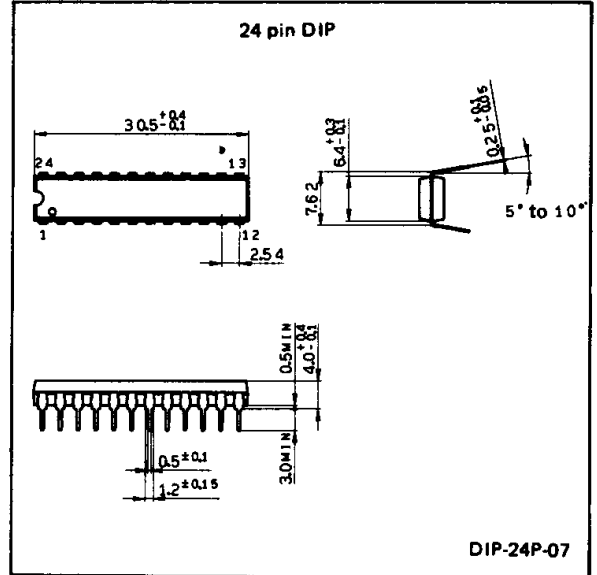
Silicon Gate CMOS IC

### Block Diagram

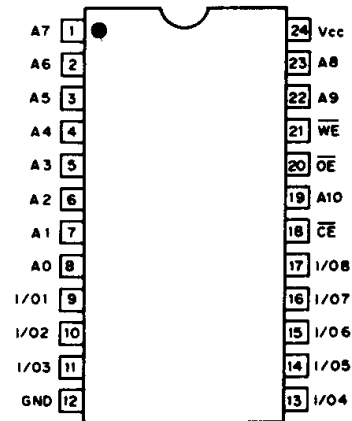


### Package Outline

Unit: mm



### Pin Configuration (Top View)



Symbol	Description
A0 to A10	Address Input
I/O1 to I/O8	Data Input Output
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
Vcc	Power Supply
GND	Ground

**Absolute Maximum Ratings**

(Ta=25°C, GND=0V)

Item	Symbol	Rating	Unit
Power Supply Voltage	V <sub>CC</sub>	-0.5* to +7.0	V
Input Voltage	V <sub>IN</sub>	-0.5* to V <sub>CC</sub> +0.5	V
Input and Output Voltage	V <sub>I/O</sub>	-0.5* to V <sub>CC</sub> +0.5	V
Allowable Power Dissipation	P <sub>D</sub>	1.0	W
Operating Temperature	T <sub>opr</sub>	0 to +70	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C
Soldering Temperature	T <sub>solder</sub>	260 ± 10	°C · sec

\* V<sub>CC</sub>, V<sub>IN</sub>, V<sub>I/O</sub> min=-3.5V for 20 ns pulse.**Truth Table**

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	Mode	I/O 1 to I/O 8	V <sub>CC</sub> Current
H	X	X	Not Selected	High Z	I <sub>SB1</sub> , I <sub>SB2</sub>
L	H	H	Output Disable	High Z	I <sub>CC1</sub> , I <sub>CC2</sub>
L	L	H	Read	DOUT	I <sub>CC1</sub> , I <sub>CC2</sub>
L	X	L	Write	DIN	I <sub>CC1</sub> , I <sub>CC2</sub>

X: "H" or "L"

**DC Recommended Operating Conditions**

(Ta=0 to +70°C, GND=0V)

Item	Symbol	Min.	Typ.*	Max.	Unit
Power Supply Voltage	V <sub>CC</sub>	4.5	5.0	5.5	V
Input High Voltage	V <sub>IH</sub>	2.2	—	V <sub>CC</sub> +0.3	V
Input Low Voltage	V <sub>IL</sub>	-0.3	—	0.8	V

\* V<sub>CC</sub>=5V, Ta=25°C

**DC and Operating Characteristics**

(V<sub>CC</sub>=5V±10%, GND=0V, T<sub>a</sub>=0 to +70°C)

Item	Symbol	Test condition	CXK5814P -35/45/55			CXK5814P -35L/45L/55L			Unit	
			Min.	Typ.	Max.	Min.	Typ.	Max.		
Input Leakage Current	I <sub>LI</sub>	V <sub>IN</sub> =GND to V <sub>CC</sub>	-2	—	2	-2	—	2	μA	
Output Leakage Current	I <sub>LO</sub>	$\overline{CE}=V_{IH}$ or $\overline{OE}=V_{IH}$ V <sub>I/O</sub> =GND to V <sub>CC</sub>	-2	—	2	-2	—	2	μA	
Operating Power Supply Current	I <sub>CC1</sub>	$\overline{CE}=V_{IL}$ I <sub>OUT</sub> =0mA V <sub>IN</sub> =V <sub>IH</sub> /V <sub>IL</sub>	35/35L	—	60	85	—	60	85	mA
			45/45L	—	50	70	—	50	70	mA
			55/55L	—	40	60	—	40	60	mA
Average Operating Current	I <sub>CC2</sub>	Cycle=Min Duty=100% I <sub>OUT</sub> =0mA	35/35L	—	70	95	—	70	95	mA
			45/45L	—	60	80	—	60	80	mA
			55/55L	—	50	70	—	50	70	mA
Standby Current	I <sub>SB1</sub>	$\overline{CE} \geq V_{CC} - 0.2V$ , V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.2V or V <sub>IN</sub> ≤ 0.2V	—	0.02	1.0	—	0.001	0.05	mA	
	I <sub>SB2</sub>	$\overline{CE}=V_{IH}$ , V <sub>IN</sub> =V <sub>IH</sub> /V <sub>IL</sub>	—	15	25	—	15	25	mA	
Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> =-4.0 mA	2.4	—	—	2.4	—	—	V	
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> =8.0 mA	—	—	0.4	—	—	0.4	V	

**Capacitance**

(T<sub>a</sub>=25°C, f=1 MHz)

Item	Symbol	Test Condition	Min.	Max.	Unit
Input Capacitance	C <sub>IN</sub>	V <sub>IN</sub> =0V	—	5	pF
Input/Output Capacitance	C <sub>I/O</sub>	V <sub>I/O</sub> =0V	—	7	pF

**Note)** This parameter is sampled and is not 100% tested.

**AC Operating Characteristics**

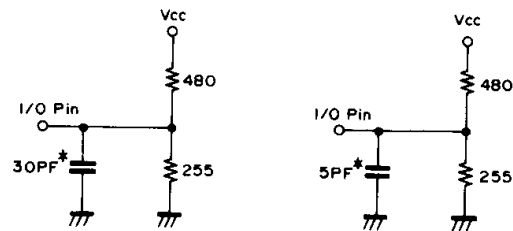
**• AC Test condition**

(V<sub>CC</sub>=5V±10%, T<sub>a</sub>=0 to +70°C)

Item	Condition
Input Pulse High Level	V <sub>IH</sub> =3.0V
Input Pulse Low Level	V <sub>IL</sub> =0V
Input Rise Time	t <sub>R</sub> =5 ns
Input Fall Time	t <sub>F</sub> =5 ns
Input and Output Timing Reference Level	1.5V
Output Load	Fig. 1

Output Load (1)

Output Load (2)\*\*



\* including scope and jig

\*\* for t<sub>LZ</sub>, t<sub>HZ</sub>, t<sub>OHZ</sub>, t<sub>OLZ</sub>, t<sub>OW</sub>, t<sub>WHZ</sub>

Fig. 1

## Read Cycle

Item	Symbol	CXK5814P -35/35L		CXK5814P -45/45L		CXK5814P -55/55L		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle Time	trc	35	—	45	—	55	—	ns
Address Access Time	tAA	—	35	—	45	—	55	ns
Chip Enable Access Time	tCO	—	35	—	45	—	55	ns
Output Enable to Output Valid	toE	—	20	—	20	—	25	ns
Output Hold from Address Change	toH	5	—	5	—	5	—	ns
Chip Enable to Output in Low Z ( $\overline{CE}$ )	tlZ*	5	—	5	—	5	—	ns
Output Enable to Output in Low Z ( $\overline{OE}$ )	tolZ*	0	—	0	—	0	—	ns
Chip Disable to Output in High Z ( $\overline{CE}$ )	thZ*	0	20	0	20	0	20	ns
Output Disable to Output in High Z ( $\overline{OE}$ )	toHZ*	0	15	0	15	0	20	ns
Chip Enable to Power Up Time	tpU	0	—	0	—	0	—	ns
Chip Disable to Power Down Time	tpD	—	30	—	30	—	30	ns

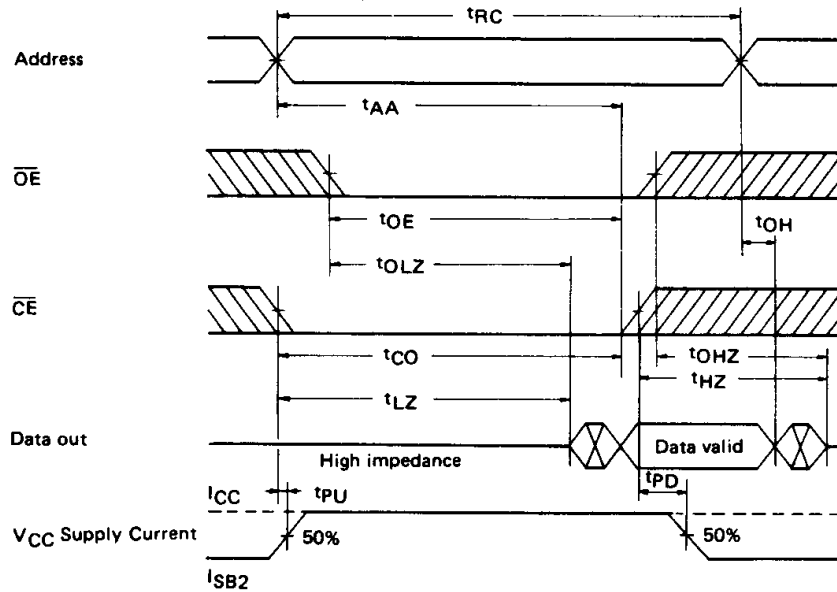
## Write Cycle

Item	Symbol	CXK5814P -35/35L		CXK5814P -45/45L		CXK5814P -55/55L		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Write Cycle Time	tWC	35	—	45	—	55	—	ns
Address Valid to End of Write	tAW	30	—	40	—	50	—	ns
Chip Enable to End of Write	tCW	30	—	40	—	50	—	ns
Data to Write Time Overlap	tdW	15	—	20	—	25	—	ns
Data Hold from Write Time	tdH	0	—	0	—	0	—	ns
Write Pulse Width	tWP	30	—	35	—	40	—	ns
Address Setup Time	tAS	0	—	0	—	0	—	ns
Write Recovery Time	tWR	0	—	0	—	0	—	ns
Output Active from End of Write	tow*	5	—	5	—	5	—	ns
Write to Output in High Z	twhZ*	0	20	0	20	0	20	ns

\*Note) Transition is measured  $\pm 500$  mV from steady state voltage with specified loading in Fig. 1. These parameters are sampled and not 100% tested.

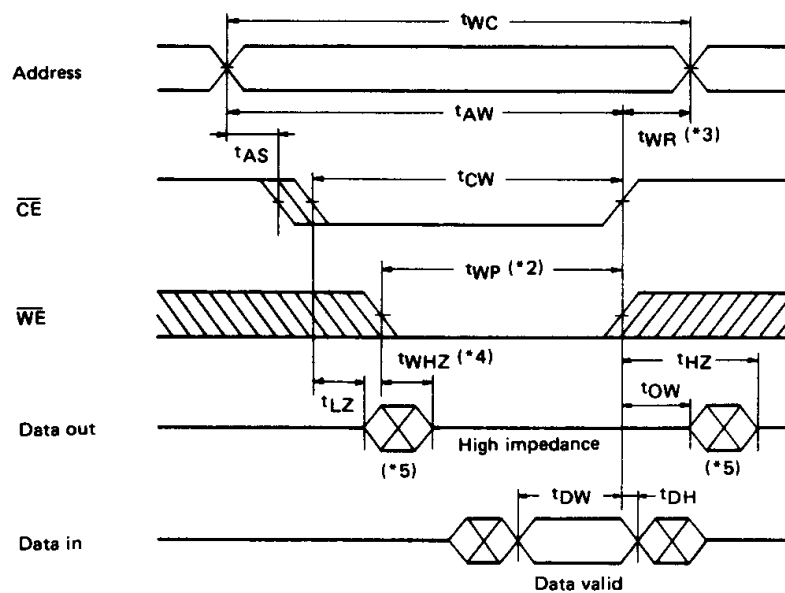
### Timing Waveform

#### (1) Read Cycle [ $\overline{WE}=V_{IH}$ ]

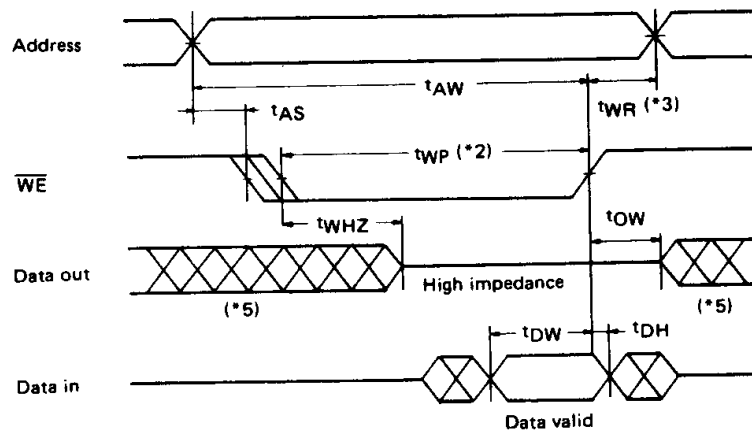


#### (2) Write Cycle

- Write Cycle No.1: [ $\overline{OE}=V_{IL}$  or  $V_{IH}$ ] (\*1)



- Write Cycle No.2: [ $\overline{OE}=V_{IL}$  or  $V_{IH}$ ,  $\overline{CE}=V_{IL}$ ] (\*1)



**\* Notes)**

1. If  $\overline{OE}$  is high, output remains in a high impedance state.
2. A write occurs during the low overlap of  $\overline{CE}$  and  $\overline{WE}$ .
3.  $t_{WR}$  is measured from the earlier of  $\overline{CE}$  or  $\overline{WE}$  going high to the end of write cycle.
4. If  $\overline{CE}$  low transition occurs simultaneously with the  $\overline{WE}$  low transition or after the  $\overline{WE}$  transition, output remains in a high impedance state.
5. During this period, I/O pins are in the output state so that the input signals of opposite phase to the output must not be applied.

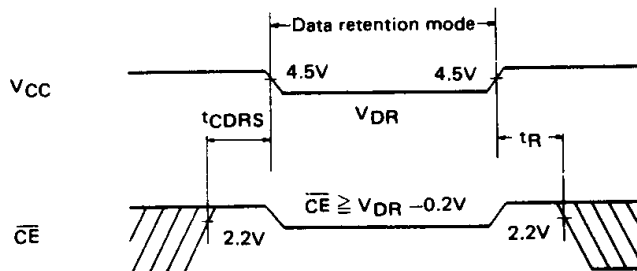
**Data Retention Characteristics**

( $T_a=0$  to  $+70^\circ\text{C}$ )

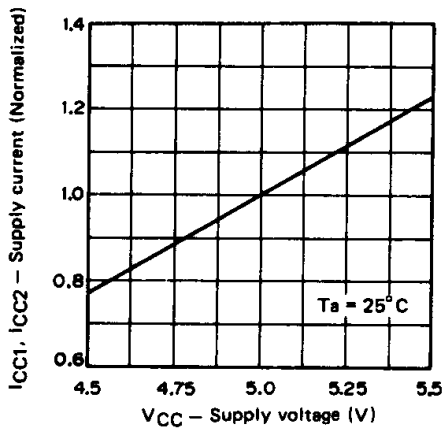
Item	Symbol	Test condition	CXK5814P -35/45/55			CXK5814P -35L/45L/55L			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Data Retention Voltage	$V_{DR}$	$\overline{CE} \geq V_{CC} - 0.2V$	2.0	5.0	5.5	2.0	5.0	5.5	V
Data Retention Current	$I_{CCDR1}$	$\overline{CE} \geq V_{CC} - 0.2V$ , $V_{CC}=3.0V$		12	600		0.6	30	$\mu\text{A}$
	$I_{CCDR2}$	$V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$ , $V_{CC}=2.0$ to $5.5V$		20	1000		1.0	50	$\mu\text{A}$
Data Retention Set up Time	$t_{CDRS}$	Chip disable to data retention mode	0			0			ns
Recovery Time	$t_R$		$t_{RC}^*$			$t_{RC}^*$			ns

\* $t_{RC}$ : Read Cycle Time

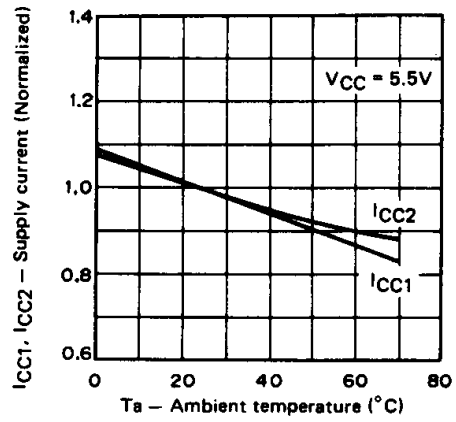
**Data Retention Waveform**



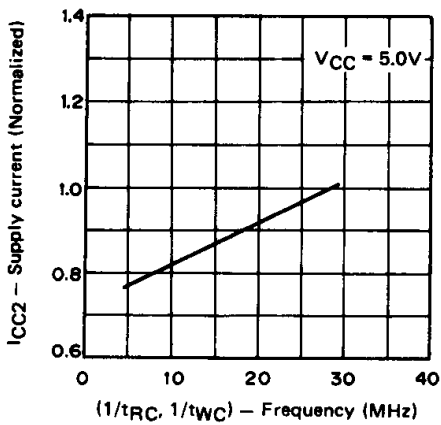
Supply current vs. Supply voltage



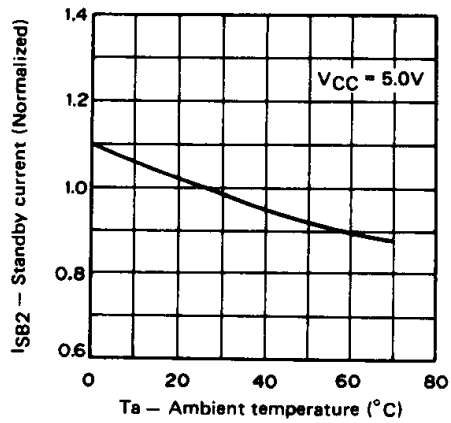
Supply current vs. Ambient temperature



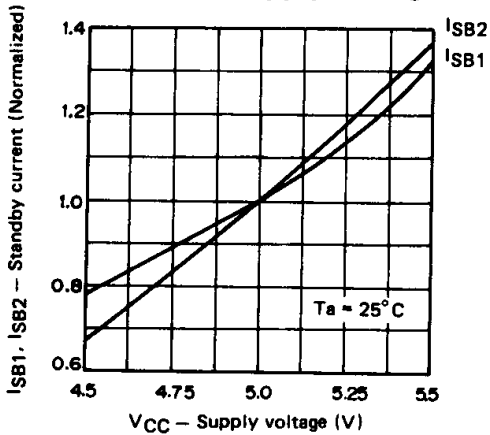
Supply current vs. Frequency



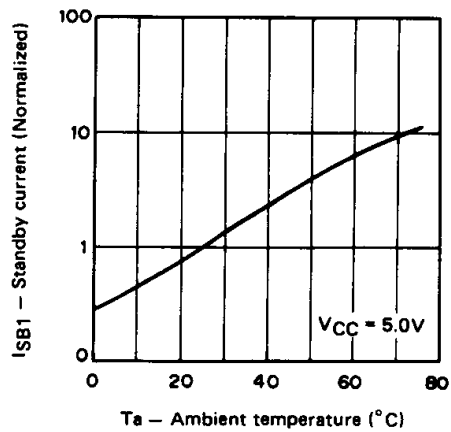
Standby current vs. Ambient temperature



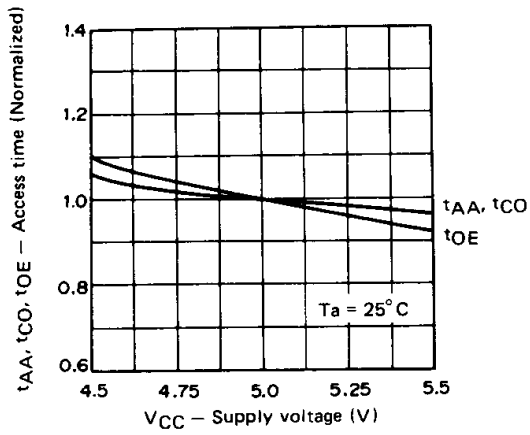
Standby current vs. Supply voltage



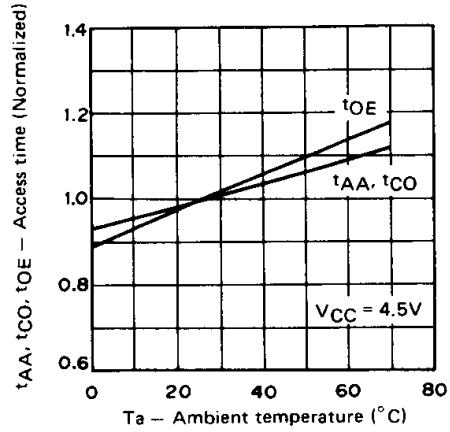
Standby current vs. Ambient temperature



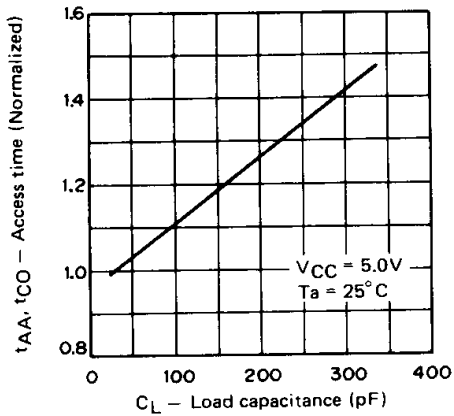
**Access time vs. Supply voltage**



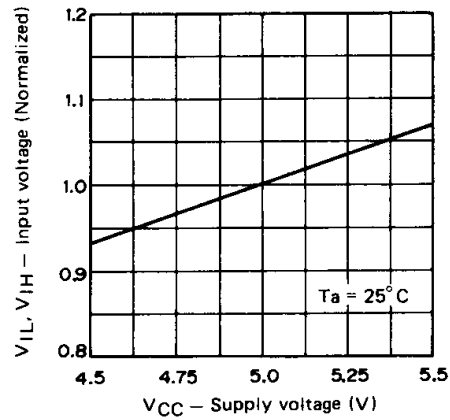
**Access time vs. Ambient temperature**



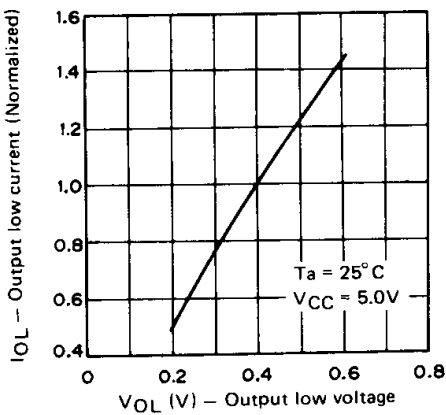
**Access time vs. Load capacitance**



**Input voltage vs. Supply voltage**



**Output current vs. Output voltage**



**Output current vs. Output voltage**

